Transistors
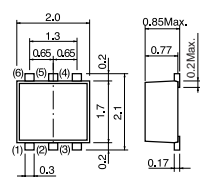
1.8V Drive Nch+Nch MOSFET

US6K4

●**Structure**

Silicon N-channel MOSFET

●**Features**

1) Two Nch MOSFETs are put in TUMT6 package.
2) High-speed switching, Low On-resistance.
3) 1.8V drive.

●**Applications**

Switching

●**Dimensions** (Unit : mm)

TUMT6

Abbreviated symbol : K04

●**Packaging specifications**

Type	Package	Taping
	Code	TR
	Basic ordering unit (pieces)	3000
US6K4		○

●**Inner circuit**

(1) Tr1 Source
(2) Tr1 Gate
(3) Tr2 Drain
(4) Tr2 Source
(5) Tr2 Gate
(6) Tr1 Drain

∗1 ESD PROTECTION DIODE
∗2 BODY DIODE

●**Absolute maximum ratings** (Ta=25°C)

<It is the same ratings for the Tr1 and Tr2>

Parameter		Symbol	Limits	Unit
Drain-source voltage		V_{DSS}	20	V
Gate-source voltage		V_{GSS}	±10	V
Drain current	Continuous	I_D	±1.5	A
	Pulsed	I_{DP} ∗1	±3.0	A
Source current (Body diode)	Continuous	I_S	0.6	A
	Pulsed	I_{SP} ∗1	2.4	A
Total power dissipation		P_D ∗2	1.0	W / TOTAL
			0.7	W / ELEMENT
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	−55 to +150	°C

∗1 Pw≤10µs, Duty cycle≤1%
∗2 Mounted on a ceramic board

●**Thermal resistance**

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth(ch-a) ∗	125	°C/W / TOTAL
		179	°C/W / ELEMENT

∗ Mounted on a ceramic board

ROHM

Transistors

●**Electrical characteristics** (Ta=25°C)

<It is the same characteristics for the Tr1 and Tr2>

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	–	–	±10	μA	V_{GS}=±10V, V_{DS}=0V
Drain-source breakdown voltage	$V_{(BR)DSS}$	20	–	–	V	I_D= 1mA, V_{GS}=0V
Zero gate voltage drain current	I_{DSS}	–	–	1	μA	V_{DS}= 20V, V_{GS}=0V
Gate threshold voltage	$V_{GS(th)}$	0.3	–	1.0	V	V_{DS}= 10V, I_D= 1mA
Static drain-source on-state resistance	$R_{DS(on)}$*	–	130	180	mΩ	I_D= 1.5A, V_{GS}= 4.5V
		–	170	240	mΩ	I_D= 1.5A, V_{GS}= 2.5V
		–	220	310	mΩ	I_D= 0.8A, V_{GS}= 1.8V
Forward transfer admittance	$|Y_{fs}|$ *	1.6	–	–	S	V_{DS}= 10V, I_D= 1.5A
Input capacitance	C_{iss}	–	110	–	pF	V_{DS}= 10V
Output capacitance	C_{oss}	–	18	–	pF	V_{GS}=0V
Reverse transfer capacitance	C_{rss}	–	15	–	pF	f=1MHz
Turn-on delay time	$t_{d(on)}$ *	–	5	–	ns	I_D= 1.0A
Rise time	t_r *	–	5	–	ns	V_{DD}≒ 10V
Turn-off delay time	$t_{d(off)}$ *	–	20	–	ns	V_{GS}= 4.5V
Fall time	t_f *	–	3	–	ns	R_L= 10Ω R_{GS}=10Ω
Total gate charge	Q_g *	–	1.8	2.5	nC	V_{DD}≒10V
Gate-source charge	Q_{gs} *	–	0.3	–	nC	V_{GS}= 4.5V
Gate-drain charge	Q_{gd} *	–	0.3	–	nC	I_D= 1.5A

＊Pulsed

●**Body diode characteristics** (Source-drain) (Ta=25°C)

<It is the same characteristics for the Tr1 and Tr2>

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{SD}	–	–	1.2	V	I_S= 0.6A, V_{GS}=0V

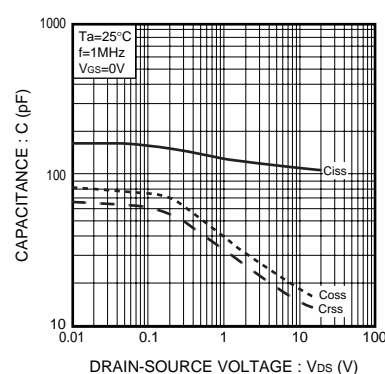●**Electrical characteristics curves**

Fig.1 Typical Capacitance
        vs. Drain-Source Voltage

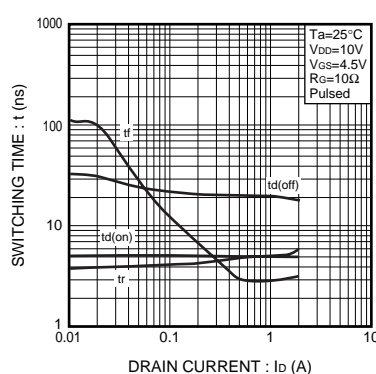

Fig.2 Switching Characteristics
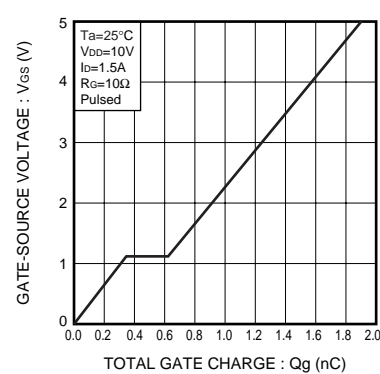

Fig.3 Dynamic Input Characteristics
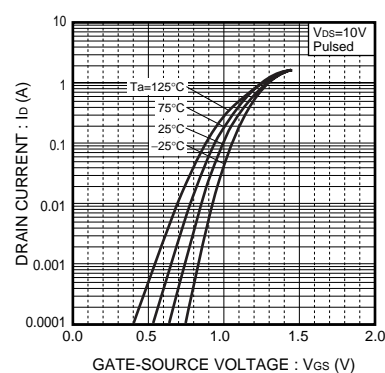

Fig.4 Typical Transfer Characteristics

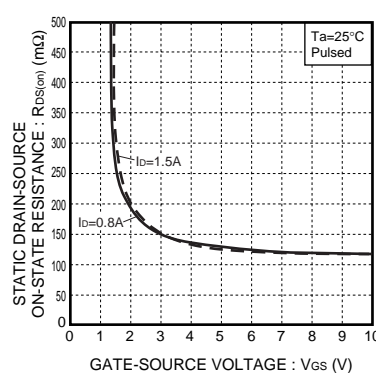
Fig.5 Static Drain-Source
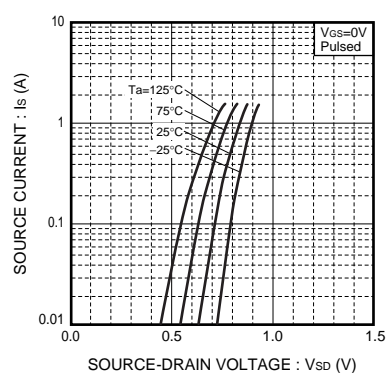   On-State Resistance vs.
        Gate-source Voltage

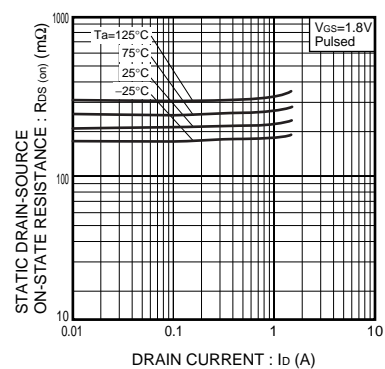
Fig.6 Source Current vs.
        Source-Drain Voltage

Fig.7 Static Drain-Source
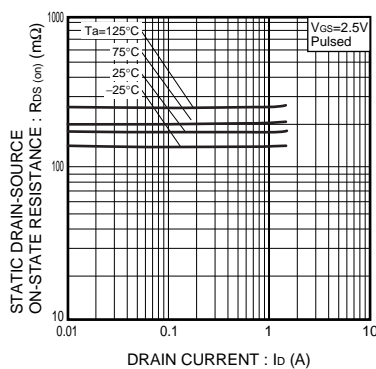   On-State Resistance
        vs. Drain Current (I)

Fig.8 Static Drain-Source
        On-State Resistance
        vs. Drain Current (II)
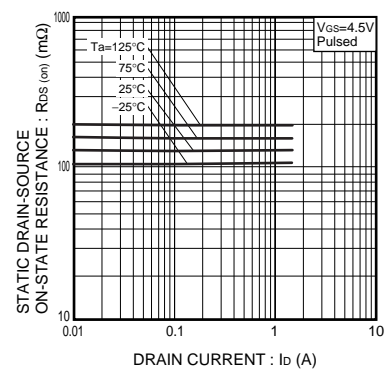
Fig.9 Static Drain-Source
        On-State Resistance
        vs. Drain Current (III)

●**Notice**

This product might cause chip aging and breakdown under the large electrified environment.
Please consider to design ESD protection circuit.

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Appendix

Thank you for your accessing to ROHM product informations.
More detail product informations and catalogs are available, please contact your nearest sales office.

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Appendix1-Rev2.0